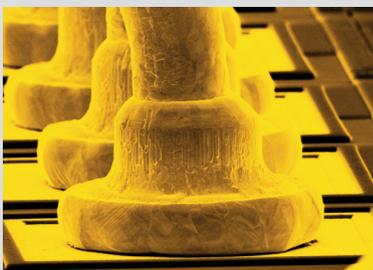
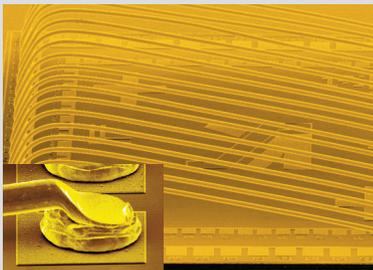
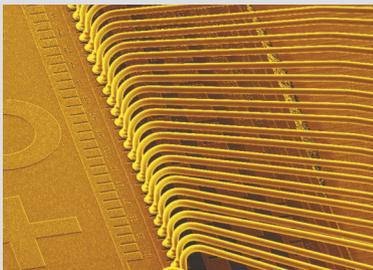


AW-14 Gold Bonding Wire for Universal Use



For the last half decade, AW-14 has been an industry mainstay for applications involving low loops such as those found in TQFP, CSP, TSOP and smart card assembly. Consistent fine grain size and a short heat affected zone allow low heights (as low as 100 μm) and long spans (up to 7 mm). This versatile 4N wire (99.99 % Au) provides very wide parameter window and can be used on virtually all types of equipment for both ball and wedge bonding.

Easy to optimize parameters for a wide range of packages

AW-14 lends itself to a variety of devices (from discretes through TSOPs, QFPs and BGAs for single die, stacked die and die-to-die applications) due to a high modulus and stable properties. AW-14's large process windows provide robust, highly portable bonding in mass production, making it one of the industry's easiest wires to use.

AW-14 Benefits

- Large process window for robust, highly portable mass production
- Proven in the widest range of applications
- Excellent low loop stability and high strength properties for a variety of advanced packaging requirements
- Consistent ball size and fine-grain, short heat affected zone (HAZ) at ball neck
- Easily optimized wire available in diameters down to 17.5 μm (0.7 mil.)
- Compatible with all ball and wedge bonding equipment

AW-14 Low Loop Consistency

All dimensions in microns

Wire Size	Loop		Std		
	Height	Dev	Min.	Max.	n
25	168	4.0	160	168	20
25	150	2.3	146	154	32
33	152	5.8	137	168	100

Bonding Conditions: Wire diameter: 25 μm (1.0 mils)
Wire bonder: K&S 1488 turbo · Package type: 208-lead QFP · Die metallization: AlSi (1%) Cu (0.5%) · Lead-frame: Ag-plated Cu · Wire span: 4 – 7 mm · Bonding temperature: 220 °C · Capillary: 414Fa-0310-R35

Recommended Technical Data of AW-14

Diameter	Microns	18	20	23	25	28	30	32	33
	Mils	0.7	0.8	0.9	1.0	1.1	1.2	1.25	1.3
Recommended Spec for Ball Bonding									
Elongation (%)		2 – 5	2 – 6	2 – 6	2 – 6	2 – 6	2 – 7	2 – 7	2 – 7
Breaking Load (g)		3 – 6	4 – 9	7 – 12	8 – 13	10 – 15	12 – 18	14 – 21	15 – 22
In-Line Pad Pitch (μm)									
Min. In-Line Pad Pitch					65	70	80		

For other diameters, please contact Heraeus Bonding Wires sales representative.

Range of recommended pad pitch with corresponding wire diameter.

AW-14 Characteristics for 25 µm diameter

Non-Gold Elements	< 100 ppm
Elastic Modulus	~ 80 GPa
Heat Affected Zone (HAZ)	50 – 190 µm
Melting Point	1063 °C
Density	19.32 g/cm ³
Heat Conductivity	3.17 W/cm-K
Electrical Resistivity	2.3 µΩ-cm
Coeff. of Linear Expansion (20 – 100 °C)	14.2 ppm/K
Fusing Current for 25 µm, dia 100 mm length (in air)	0.37 A

Superior Loop Linearity

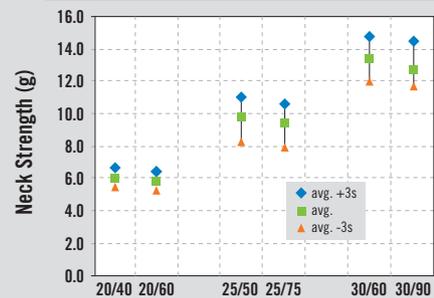
Mold Sweep Resistance

- Auto-Gang Pot Molding
- Sumitomo Compound EME 7320
- Wire diameter 30 µm, wire span up to 7 mm
- Spec. limit 8 % of wire span

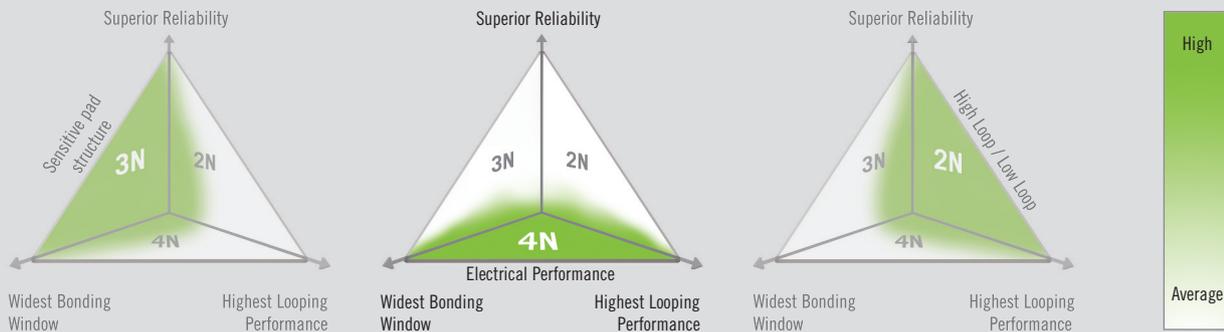
DAP Size	Wire Span	Std			
		Avg.	Dev.	Min.	Max.
9 x 9	5 mm	1.2	0.40	0.3	2.1
10.5 x 10.5	6 mm	1.9	0.67	0.8	3.3
12 x 12	7 mm	2.0	0.59	0.8	3.4

Data is in % of wire span, measured at 90 ° positioned to gate.

Neck Strength



Gold Wire Segmentation by Properties



Heraeus Electronics
 Heraeus Deutschland GmbH & Co. KG
 Heraeusstraße 12-14
 63450 Hanau, Germany
www.heraeus-electronics.com

Americas
 Phone +1 610 825 6050
electronics.americas@heraeus.com

Asia Pacific
 Phone +65 6571 7677
electronics.apac@heraeus.com

China
 Phone +86 21 3357 5457
electronics.china@heraeus.com

Europe, Middle East and Africa
 Phone +49 6181 35 3069
 +49 6181 35 3627
electronics.emea@heraeus.com